



#### FMMT734

#### **100V PNP DARLINGTON TRANSISTOR IN SOT23**

#### **Features**

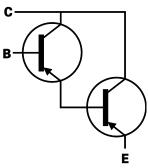
- BV<sub>CEO</sub> > -100V
- I<sub>C</sub> = -800mA High Continuous Collector Current
- Darlington Transistor h<sub>FE</sub> > 20k @ 100mA for High Gain
- High Gain Hold-Up to 5A
- 625mW Power Dissipation
- Complementary Darlington NPN Type: FMMT634
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

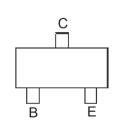
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 @3
- Weight 0.008 grams (Approximate)







Device Symbol



Top View Pin-Out

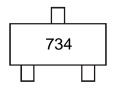
### **Ordering Information** (Note 4)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
FMMT734TA	AEC-Q101	734	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



734 = Product Type Marking Code



### Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	-100	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-100	V
Emitter-Base Voltage	$V_{EBO}$	-12	V
Continuous Collector Current	Ic	-800	mA
Peak Pulse Current	Ісм	-5	Α

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P <sub>D</sub>	625	mW
Power Dissipation (Note 6)	P <sub>D</sub>	806	mW
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	200	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	155	°C/W
Thermal Resistance, Junction to Leads (Note 7)	R <sub>θJL</sub>	194	°C/W
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

## ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	2,000	V	1C
Electrostatic Discharge - Machine Model	ESD MM	200	V	Α

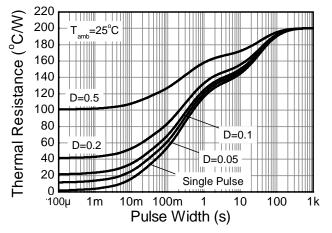
Notes:

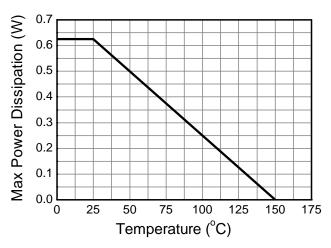
- 5. For a device surface mounted on 25mm X 25mm FR-4 PCB with high coverage of single sided 1 oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
  6. Same as note 5, except the device is measured at t ≤ 5 sec.
  7. Thermal resistance from junction to solder-point (at the end of the collector lead).

- 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

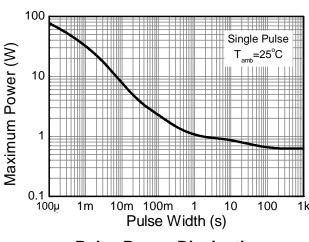


## **Thermal Characteristics and Derating Information**

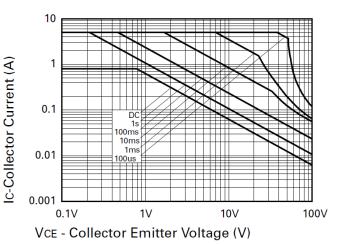




## **Transient Thermal Impedance**



**Derating Curve** 



**Pulse Power Dissipation** 

Safe Operating Area



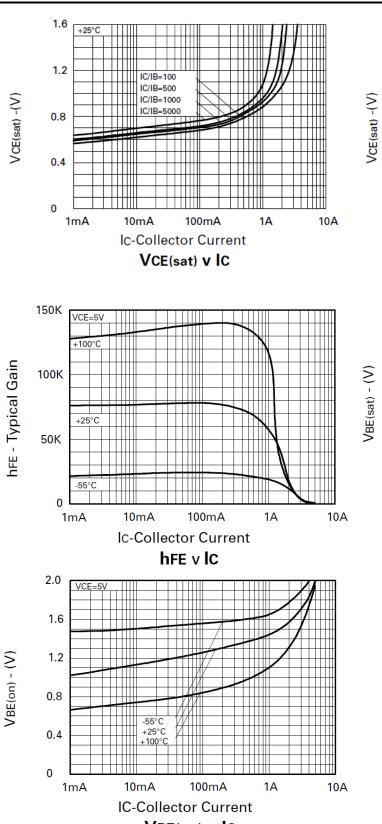
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

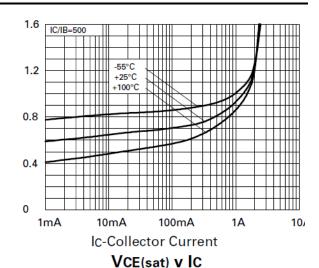
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	$BV_{CBO}$	-100	-130	-	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	-100	-116	-	V	$I_C = -5mA$
Emitter-Base Breakdown Voltage	$BV_{EBO}$	-12	-17	-	V	$I_E = -100 \mu A$
Collector Cutoff Current	I <sub>CBO</sub>	-	-	-10	nA	V <sub>CB</sub> = -80V
Collector Cutoff Current	I <sub>CES</sub>	-	-	-200	nA	V <sub>CES</sub> = -80V
Emitter Cutoff Current	I <sub>EBO</sub>	-	-	-10	nA	V <sub>EB</sub> = -7V
ON CHARACTERISTICS (Note 9)						
Static Forward Current Transfer Ratio  Collector-Emitter Saturation Voltage	h <sub>FE</sub>	- 20,000 15,000 5,000 - -	60,000 60,000 50,000 15,000 150 20,000 -0.68 -0.72 -0.78 -0.86 -0.72 -0.90	- - - - - - -0.75 -0.80 -0.86 -0.97 - -1.05	- V	Ic = -10mA, V <sub>CE</sub> = -5V Ic = -100mA, V <sub>CE</sub> = -5V Ic = -1A, V <sub>CE</sub> = -5V Ic = -2A, V <sub>CE</sub> = -5V Ic = -5A, V <sub>CE</sub> = -5V Ic = -1A, V <sub>CE</sub> = -2V Ic = -100mA, I <sub>B</sub> = -1mA Ic = -250mA, I <sub>B</sub> = -1mA Ic = -500mA, I <sub>B</sub> = -5mA Ic = -800mA, I <sub>B</sub> = -5mA Ic = -800mA, I <sub>B</sub> = -5mA Ic = -800mA, I <sub>B</sub> = -5mA
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	-	-1.6	-1.75	V	$I_C = -1A$ , $I_B = -5mA$
Base-Emitter Turn-On Voltage	V <sub>BE(on)</sub>	-	-1.3	-1.75	V	I <sub>C</sub> = -1A, V <sub>CE</sub> =-5V
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f <sub>T</sub>	-	140	-	MHz	V <sub>CE</sub> = -10V, I <sub>C</sub> = -10mA, f = 100MHz
Output Capacitance	C <sub>obo</sub>	-	14	25	pF	$V_{CB} = -10V$ , $f = 1MHz$
Turn-On Time	t <sub>(on)</sub>	-	460	-	ns	I <sub>C</sub> =-500mA, V <sub>CC</sub> =-20V
Turn-Off Time	t <sub>(off)</sub>	-	1200	-	ns	$I_B=\pm 1 mA$

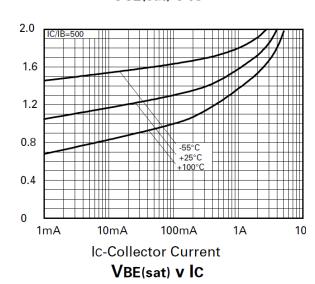
Note: 9. Measured under pulsed conditions. Pulse width  $\leq$  300µs. Duty cycle  $\leq$  2%.



## Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)





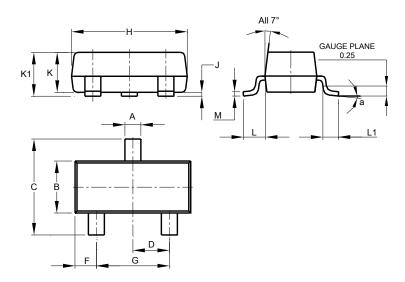




## **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

#### SOT23

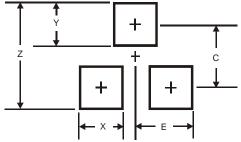


SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
C	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
K	0.890	1.00	0.975		
K1	0.903	1.10	1.025		
L	0.45	0.61	0.55		
L1	0.25	0.55	0.40		
М	0.085	0.150	0.110		
а	8°				
All Dimensions in mm					

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.





Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
E	1.35

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.



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